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100V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Max R _{DS(ON)}	Package	Max I _D T _A = +25°C
-100V	1Ω @ V _{GS} = -10V	SOT23	-0.7A
-100 V	1.45Ω @ V _{GS} = -6.0V	30123	-0.5A

Description

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- **Power Management Functions**
- **Disconnect Switches**
- Motor Control

Features

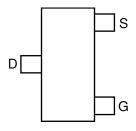
- Fast Switching Speed
- Low Input Capacitance
- Low Gate Charge
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Data Sheet (ZXMP10A13FQ)

Mechanical Data

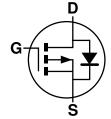
- Case: SOT23
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.009 grams (Approximate)



Top View



Top View Pin Out



Equivalent Circuit

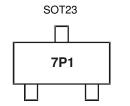
Ordering Information (Note 4)

- 7			
	Part Number	Case	Packaging
	ZXMP10A13FTA	SOT23	3,000/Tape & Reel
	ZXMP10A13FTC	SOT23	10.000/Tane & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



7P1 = Product Type Marking Code



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				V_{DSS}	-100	V
Gate-Source Voltage				V _{GS}	±20	V
Continuous Drain Current	V _{GS} = 10V	T _A = +70°C	(Note 6) (Note 6) (Note 6)	l _D	-0.7 -0.5 -0.6	А
Pulsed Drain Current (Note 7)				I _{DM}	-3.1	Α
Continuous Source Current (Body Diode) (Note 5)				Is	-1.1	Α
Pulsed Source Current (Body Diode) (Note 7)				I _{SM}	-3.1	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	625	mW
Linear Derating Factor	FD	5	mW/°C
Power Dissipation (Note 6)	D-	806	mW
Linear Derating Factor	P _D	6.4	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R _{0JL}	194	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

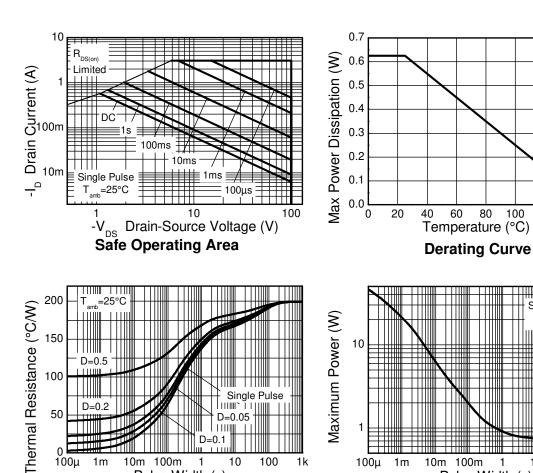
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. For a device surface mounted on FR4 PCB measured at t ≤5 secs.
 7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10µs pulse current limited by maximum junction temperature.

- 8. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics (Continued)



Pulse Width (s) **Transient Thermal Impedance**

10m 100m 1

Pulse Power Dissipation

10m 100m 1 1 Pulse Width (s)

100μ

60

80

100

120

140 160



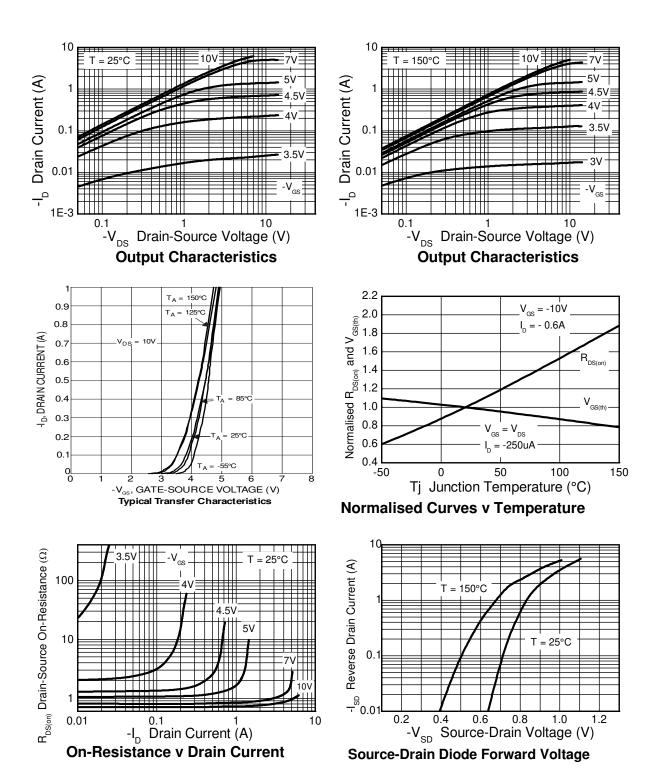
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-100	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	-2.0		-4.0	V	$I_D = -250 \mu A, \ V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	D			1.0	Ω	$V_{GS} = -10V, I_D = -0.6A$	
Static Diam-Source Off-Resistance (Note 9)	R _{DS(ON)}		_	1.45	12	$V_{GS} = -6.0V, I_D = -0.5A$	
Forward Transconductance (Notes 9 & 11)	g FS	_	1.2	_	S	$V_{DS} = -15V, I_D = -0.6A$	
Diode Forward Voltage (Note 9)	V_{SD}	_	-0.85	-0.95	V	$T_J = +25$ °C, $I_S = -0.75$ A, $V_{GS} = 0$ V	
Reverse Recovery Time (Note 11)	t _{RR}	_	29	_	ns	$T_J = +25$ °C, $I_F = -0.9$ A,	
Reverse Recovery Charge (Note 11)	Q _{RR}	_	31	_	nC	nC di/dt = 100A/μs	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C _{ISS}		141	_			
Output Capacitance	Coss		13.1	_	pF	$V_{DS} = -50V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{RSS}	_	10.8	_			
Turn-On Delay Time (Note 10)	t _{D(ON)}	_	1.6	_			
Turn-On Rise Time (Note 10)	t _R	_	2.1	_		$V_{DD} = -50V, I_D = -1.0A,$	
Turn-Off Delay Time (Note 10)	t _{D(OFF)}	_	5.9	_	ns	$R_G\cong 6.0\Omega,\ V_{GS}=-10V$	
Turn-Off Fall Time (Note 10)	t _F	_	3.3	_			
Total Gate Charge (Note 10)	Q_{G}	_	1.8	_	nC	$V_{DS} = -50V$, $V_{GS} = -5.0V$, $I_{D} = -0.6A$	
Total Gate Charge (Note 10)	Q_{G}	_	3.5	_			
Gate-Source Charge (Note 10)	Q _{GS}	_	0.6		nC	$V_{DS} = -50V, V_{GS} = -10V,$	
Gate-Drain Charge (Note 10)	Q_{GD}	_	1.6	_	I _D = -0.6A		

Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.
 For design aid only, not subject to production testing.

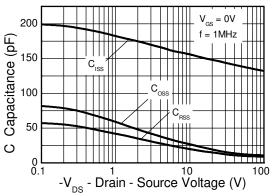


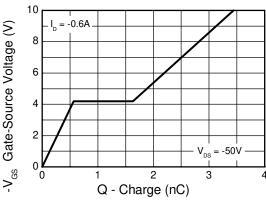
Typical Characteristics





Typical Characteristics (Continued)

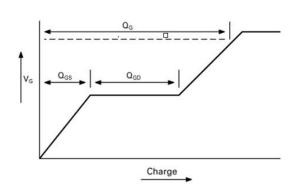




Capacitance v Drain-Source Voltage

Gate-Source Voltage v Gate Charge

Test Circuits



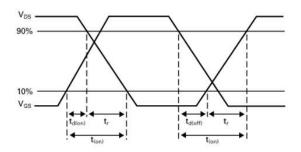
Current regulator

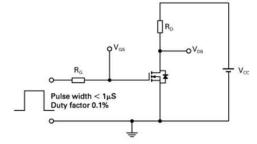
Same as D.U.T

Vos

Basic gate charge waveform

Gate charge test circuit





Switching time waveforms

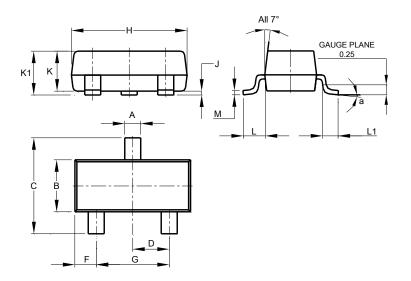
Switching time test circuit



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

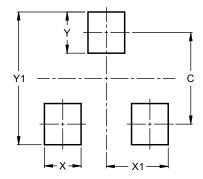


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°	_		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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